

SSP AND DSP WAFERS FOR RF DEVICES (RFSI®)

ENGINEERED ULTRA HIGH RESISTIVITY WAFERS

>10 kOhm-cm resistivity and added trap-rich layer, premium close to zero-loss substrate. > For RF filter devices

ENGINEERED HIGH RESISTIVITY WAFERS

Up to >7 kOhm-cm resistivity with added trap-rich layer, extremely low loss substrate. > For RF filter devices

UF-RFSI® WAFERS

Up to >7 kOhm-cm resistivity, trap-rich layer and Ultra Flat properties, low loss substrate > For TF-SAW

HIGH RESISTIVITY WAFERS

Up to >7 kOhm-cm resistivity without trap-rich layer. > Low loss substrate for RF IPD or integrated RFFE / RFIC

RF / POWER GAN SUBSTRATE WAFERS (SI AND SOI)

From standard to extra thick <111> Si and SOI wafers with advanced stress management for GaN growth. Customized for GaN-on-Si and GaN-on-SOI device needs. Adjustable resistivity.

> Highly functional and cost-effective challenger for GaN-on-SiC substrates. Suitable for GaN HEMT devices

SSP AND DSP WAFERS FOR MEMS AND DISCRETE POWER DEVICES

Freely adjustable wafer parameters and down to <0.001 Ohm-cm resistivity.

> For pressure and inertial sensors, varied MEMS devices

> For discrete power devices (IGBTs and Power MOSFETs with low on-resistance)

BONDED SOI WAFERS

BSOI WAFERS

Fully customizable Bonded SOI wafer with thick or thin device layer. > For traditional MEMS devices

E-SOI® WAFERS

Bonded SOI wafer with highly uniform device layer thickness tolerance of $\pm 0.1 \mu\text{m}$.

> For silicon photonics, high-precision silicon-based MEMS.

C-SOI® WAFERS

Bonded SOI with embedded / buried cavities. Fully in-house C-SOI® process.

> For pressure and inertial sensors, silicon speakers, ultrasonic transducers, resonators and microfluidic devices etc.

TERRACE FREE SOI WAFERS

200 mm BSOI, E-SOI® and Power Management SOI wafers with maximized usable area

POWER MANAGEMENT SOI WAFERS

Bonded SOI wafers with customizable dimensions and resistivity, optimized oxygen concentration and low defect density.

> For gate drivers, Battery and Power Management ICs, IPMs and other Smart Power devices

HIGH RESISTIVITY SOI WAFERS

Bonded - BSOI or suspended C-SOI® low loss structures per customer design. > For BAW resonators

TSV WAFERS

Polysilicon filled Through Silicon Vias (TSVs) enable isolated electrical connections through silicon wafers.

